

BU406, BU407

NPN Power Transistors

These devices are high voltage, high speed transistors for horizontal deflection output stages of TV's and CRT's.

Features

- High Voltage
- Fast Switching Speed
- Low Saturation Voltage
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	BU406 BU407	V_{CEO} 200 150	Vdc
Collector-Emitter Voltage	BU406 BU407	V_{CEV} 400 330	Vdc
Collector-Base Voltage	BU406 BU407	V_{CBO} 400 330	Vdc
Emitter-Base Voltage		V_{EBO} 6	Vdc
Collector Current – Continuous – Peak Repetitive		I_C 7 10	Adc
Collector Current – Peak (10 ms)		I_{CM} 15	Adc
Base Current		I_B 4	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C		P_D 60 0.48	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Storage		T_J, T_{stg} –65 to 150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.08	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	70	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	T_L	260	$^\circ\text{C}$

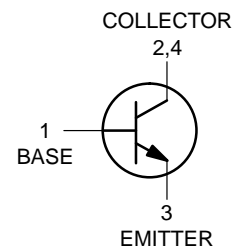


ON Semiconductor®

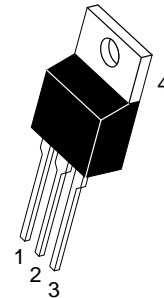
www.onsemi.com

NPN SILICON POWER TRANSISTORS 7 AMPERES – 60 WATTS 150 AND 200 VOLTS

SCHEMATIC



MARKING DIAGRAM



TO-220
CASE 221A
STYLE 1



BU40x = Specific Device Code
x = 6 or 7
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
BU406G	TO-220AB (Pb-Free)	50 Units / Rail
BU407G	TO-220AB (Pb-Free)	50 Units / Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BU406, BU407

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit	
OFF CHARACTERISTICS						
Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 100\text{ mAdc}$, $I_B = 0$)	BU406 BU407	$V_{CEO(sus)}$	200 150	- -	- -	Vdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEV}$, $V_{BE} = 0$) ($V_{CE} = \text{Rated } V_{CEO} + 50\text{ Vdc}$, $V_{BE} = 0$) ($V_{CE} = \text{Rated } V_{CEO} + 50\text{ Vdc}$, $V_{BE} = 0$, $T_C = 150^\circ\text{C}$)		I_{CES}	- - -	- - -	5 0.1 1	mAdc
Emitter Cutoff Current ($V_{EB} = 6\text{ Vdc}$, $I_C = 0$)	BU406, BU407	I_{EBO}	-	-	1	mAdc
ON CHARACTERISTICS (Note 1)						
Collector-Emitter Saturation Voltage ($I_C = 5\text{ Adc}$, $I_B = 0.5\text{ Adc}$)		$V_{CE(sat)}$	-	-	1	Vdc
Base-Emitter Saturation Voltage ($I_C = 5\text{ Adc}$, $I_B = 0.5\text{ Adc}$)		$V_{BE(sat)}$	-	-	1.2	Vdc
Forward Diode Voltage ($I_{EC} = 5\text{ Adc}$) "D" only		V_{EC}	-	-	2	Volts
DYNAMIC CHARACTERISTICS						
Current-Gain - Bandwidth Product ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f_{test} = 20\text{ MHz}$)		f_T	10	-	-	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1\text{ MHz}$)		C_{ob}	-	80	-	pF
SWITCHING CHARACTERISTICS						
Inductive Load Crossover Time ($V_{CC} = 40\text{ Vdc}$, $I_C = 5\text{ Adc}$, $I_{B1} = I_{B2} = 0.5\text{ Adc}$, $L = 150\ \mu\text{H}$)		t_c	-	-	0.75	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 1\%$.

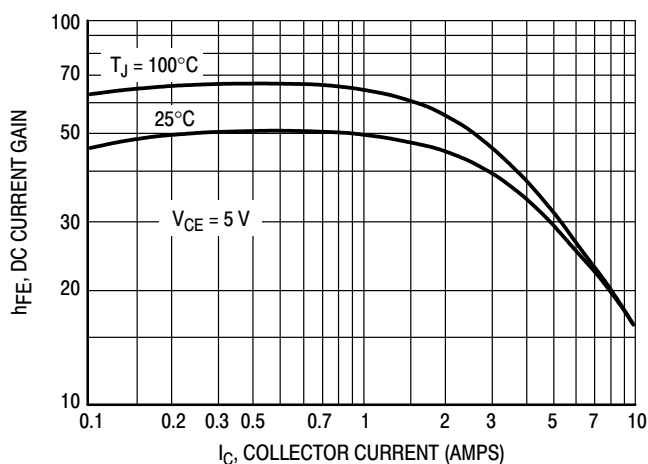


Figure 1. DC Current Gain

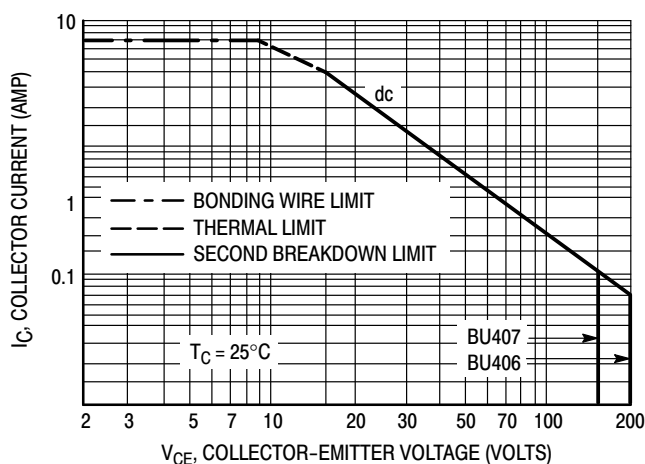
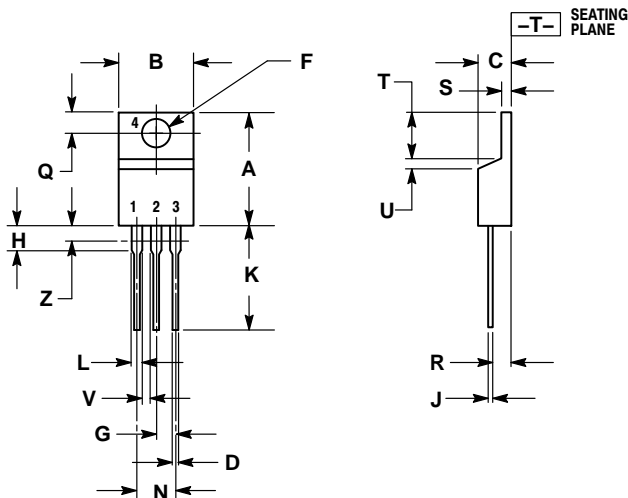


Figure 2. Maximum Rated Forward Bias Safe Operating Area

BU406, BU407

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AH



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

ON Semiconductor and the are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative